

CMXT2222A

SURFACE MOUNT
DUAL NPN
SILICON TRANSISTORS



www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMXT2222A type is a dual NPN silicon transistor manufactured by the epitaxial planar process, epoxy molded in a SUPERmini™ surface mount package, and designed for small signal general purpose and switching applications.

MARKING CODE: X1P

SUPERmini™



SOT-26 CASE

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

Collector-Base Voltage
Collector-Emitter Voltage
Emitter-Base Voltage
Continuous Collector Current
Power Dissipation
Operating and Storage Junction Temperature
Thermal Resistance

SYMBOL

V_{CBO} 75
 V_{CEO} 40
 V_{EBO} 6.0
 I_C 600
 P_D 350
 T_J, T_{stg} -65 to +150
 θ_{JA} 357

UNITS

V
V
V
mA
mW
 $^\circ\text{C}$
 $^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS PER TRANSISTOR: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_{CBO}	$V_{CB}=60V$		10	nA
I_{CBO}	$V_{CB}=60V, T_A=125^\circ\text{C}$		10	μA
I_{CEV}	$V_{CE}=60V, V_{EB}=3.0V$		10	nA
I_{EBO}	$V_{EB}=3.0V$		10	nA
BV_{CBO}	$I_C=10\mu\text{A}$	75		V
BV_{CEO}	$I_C=10\text{mA}$	40		V
BV_{EBO}	$I_E=10\mu\text{A}$	6.0		V
$V_{CE(SAT)}$	$I_C=150\text{mA}, I_B=15\text{mA}$		0.3	V
$V_{CE(SAT)}$	$I_C=500\text{mA}, I_B=50\text{mA}$		1.0	V
$V_{BE(SAT)}$	$I_C=150\text{mA}, I_B=15\text{mA}$	0.6	1.2	V
$V_{BE(SAT)}$	$I_C=500\text{mA}, I_B=50\text{mA}$		2.0	V
h_{FE}	$V_{CE}=10V, I_C=0.1\text{mA}$	35		
h_{FE}	$V_{CE}=10V, I_C=1.0\text{mA}$	50		
h_{FE}	$V_{CE}=10V, I_C=10\text{mA}$	75		
h_{FE}	$V_{CE}=10V, I_C=150\text{mA}$	100	300	
h_{FE}	$V_{CE}=1.0V, I_C=150\text{mA}$	50		
h_{FE}	$V_{CE}=10V, I_C=500\text{mA}$	40		
f_T	$V_{CE}=20V, I_C=20\text{mA}, f=100\text{MHz}$	300		MHz
C_{ob}	$V_{CB}=10V, I_E=0, f=1.0\text{MHz}$		8.0	pF
C_{ib}	$V_{EB}=0.5V, I_C=0, f=1.0\text{MHz}$		25	pF
h_{ie}	$V_{CE}=10V, I_C=1.0\text{mA}, f=1.0\text{kHz}$	2.0	8.0	k Ω
h_{ie}	$V_{CE}=10V, I_C=10\text{mA}, f=1.0\text{kHz}$	0.25	1.25	k Ω

R3 (12-February 2010)

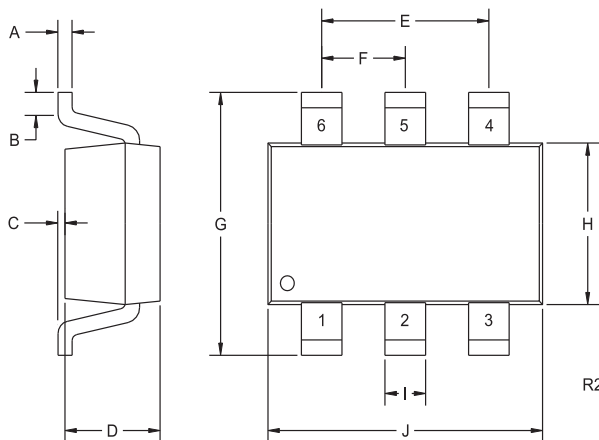
CMXT2222A
SURFACE MOUNT
DUAL NPN
SILICON TRANSISTORS



ELECTRICAL CHARACTERISTICS PER TRANSISTOR - Continued: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
h_{re}	$V_{CE}=10\text{V}, I_C=1.0\text{mA}, f=1.0\text{kHz}$		8.0	$\times 10^{-4}$
h_{re}	$V_{CE}=10\text{V}, I_C=10\text{mA}, f=1.0\text{kHz}$		4.0	$\times 10^{-4}$
h_{fe}	$V_{CE}=10\text{V}, I_C=1.0\text{mA}, f=1.0\text{kHz}$	50	300	
h_{fe}	$V_{CE}=10\text{V}, I_C=10\text{mA}, f=1.0\text{kHz}$	75	375	
h_{oe}	$V_{CE}=10\text{V}, I_C=1.0\text{mA}, f=1.0\text{kHz}$	5.0	35	μS
h_{oe}	$V_{CE}=10\text{V}, I_C=10\text{mA}, f=1.0\text{kHz}$	25	200	μS
$rb'C_c$	$V_{CB}=10\text{V}, I_E=20\text{mA}, f=31.8\text{MHz}$		150	ps
NF	$V_{CE}=10\text{V}, I_C=100\mu\text{A}, R_S=1.0\text{k}\Omega, f=1.0\text{kHz}$		4.0	dB
t_d	$V_{CC}=30\text{V}, V_{BE}=0.5\text{V}, I_C=150\text{mA}, I_{B1}=15\text{mA}$		10	ns
t_r	$V_{CC}=30\text{V}, V_{BE}=0.5\text{V}, I_C=150\text{mA}, I_{B1}=15\text{mA}$		25	ns
t_s	$V_{CC}=30\text{V}, I_C=150\text{mA}, I_{B1}=I_{B2}=15\text{mA}$		225	ns
t_f	$V_{CC}=30\text{V}, I_C=150\text{mA}, I_{B1}=I_{B2}=15\text{mA}$		60	ns

SOT-26 CASE - MECHANICAL OUTLINE



SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.004	0.007	0.11	0.19
B	0.016	-	0.40	-
C	-	0.004	-	0.10
D	0.039	0.047	1.00	1.20
E	0.074	0.075	1.88	1.92
F	0.037	0.038	0.93	0.97
G	0.102	0.118	2.60	3.00
H	0.059	0.067	1.50	1.70
I	0.016		0.41	
J	0.110	0.118	2.80	3.00

SOT-26 (REV: R2)

LEAD CODE:

- 1) Emitter Q1
- 2) Base Q1
- 3) Collector Q2
- 4) Emitter Q2
- 5) Base Q2
- 6) Collector Q1

MARKING CODE: X1P

R3 (12-February 2010)

OUTSTANDING SUPPORT AND SUPERIOR SERVICES



PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- Inventory bonding
- Consolidated shipping options
- Custom bar coding for shipments
- Custom product packing

DESIGNER SUPPORT/SERVICES

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free quick ship samples (2nd day air)
- Online technical data and parametric search
- SPICE models
- Custom electrical curves
- Environmental regulation compliance
- Customer specific screening
- Up-screening capabilities
- Special wafer diffusions
- PbSn plating options
- Package details
- Application notes
- Application and design sample kits
- Custom product and package development

REQUESTING PRODUCT PLATING

1. If requesting Tin/Lead plated devices, add the suffix "TIN/LEAD" to the part number when ordering (example: 2N2222A TIN/LEAD).
2. If requesting Lead (Pb) Free plated devices, add the suffix "PBFREE" to the part number when ordering (example: 2N2222A PBFREE).

CONTACT US

Corporate Headquarters & Customer Support Team

Central Semiconductor Corp.
145 Adams Avenue
Hauppauge, NY 11788 USA
Main Tel: (631) 435-1110
Main Fax: (631) 435-1824
Support Team Fax: (631) 435-3388
www.centrasemi.com

Worldwide Field Representatives:
www.centrasemi.com/wwreps

Worldwide Distributors:
www.centrasemi.com/wwdistributors

For the latest version of Central Semiconductor's **LIMITATIONS AND DAMAGES DISCLAIMER**, which is part of Central's Standard Terms and Conditions of sale, visit: www.centrasemi.com/terms